

IN THE ABSTRACT

Please amend the abstract as follows:

The present invention describes a method for fabricating micro-devices comprising ~~aluminum oxide~~ aluminum oxide-structures without the need for an extra lithographical processing step. So, no extra mask is needed. It appears that under certain circumstances, ~~aluminum oxide~~ aluminum oxide walls arise in the etching process, just above sloped walls of underlying metal structures. The fact that the walls of the metal structures are sloped, is essential here. Using the method according to the invention, ~~aluminum oxide~~ aluminum oxide structures can be fabricated that are aligned exactly above the sloped walls of the metal structure. These aligned ~~aluminum oxide~~ aluminum oxide structures can be used as walls in for example microfluidic channels, electrowetting displays, electrophoretic displays or field emitting displays.